SKiiP 792 GB 170 - 373 CTV

Absolute Maximum Ratings			
Symbol	**Conditions** [1]	**Values**	**Units**
V_{isol} [4]	AC, 1min	4000	V
T_{op} , T_{stg}	Operating / stor. temperature	-25...+85	°C
IGBT and InverseDiode			
V_{CES}		1700	V
V_{CC} [5]	Operating DC link voltage	1200	V
I_C	IGBT	750	A
T_j [3]	IGBT + Diode	-40...+150	°C
I_F	Diode	750	A
I_{FM}	Diode, t_p < 1 ms	1500	A
I_{FSM}	Diode, T_j = 150 °C, 10ms; sin	6480	A
I^2t (Diode)	Diode, T_j = 150 °C, 10ms	210	kAs^2
Driver			
V_{S1}	Stabilized Power Supply	18	V
V_{S2}	Non-stabilized Power Supply	30	V
f_{smax}	Switching frequency	11,0	kHz
dV/dt	Primary to secondary side	75	kV/µs

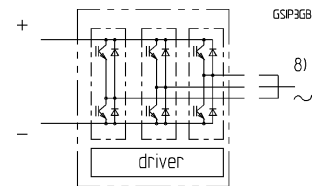
Characteristics						
Symbol	**Conditions** [1]		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{(BR)CES}$	Driver without supply		≥V_{CES}	–	–	V
I_{CES}	V_{GE} = 0,	T_j = 25 °C	–	–	3	mA
	V_{CE} = V_{CES}	T_j = 125 °C	–	45	–	mA
V_{CE0}	T_j = 125 °C		–	1,77	–	V
r_C	T_j = 125 °C		–	5,5	–	mΩ
V_{Cesat}	I_C = 600A,	T_j = 125 °C	–	5,1	–	V
V_{Cesat}	I_C = 600A,	T_j = 25 °C	–	–	3,85	V
E_{on} + E_{off}	V_{CC}=900/1200V, I_C=750A T_j = 125 °C		–	634/976	–	mJ
C_{CHC}	per SkiiP, AC side		–	2,4	–	nF
L_{CE}	Top, Bottom		–	5	–	nH
Inverse Diode [2]						
V_F = V_{EC}	I_F= 600A;	T_j = 125 °C	–	1,89	–	V
V_F= V_{EC}	I_F= 600A;	T_j = 25 °C	–	–	2,90	V
E_{on} + E_{off}	I_F= 750A;	T_j = 125 °C	–	90	–	mJ
V_{TO}	T_j = 125 °C		–	0,90	–	V
r_T	T_j = 125 °C		–	1,6	–	mΩ
Thermal Characteristics						
R_{thjs} [10]	per IGBT		–	–	0,027	°C/W
R_{thjs} [10]	per Diode		–	–	0,089	°C/W
R_{thsa} [6,10]	P16 heatsink; see case S3		–	–	0,036	°C/W
Driver						
I_{S1}	Supply current 15V-supply		260+590*f_s /f_{smax}+1,3*I_{AC}/A			mA
I_{S2}	Supply current 24V-supply		200+430*f_s /f_{smax}+1,0*I_{AC}/A			mA
$t_{interlock-driver}$	Interlock-time			3,0		µs
SKiiPPACK protection						
I_{TRIPSC}	Short circuit protection			938 ± 2%		A
I_{TRIPLG}	Ground fault protection			-		A
T_{TRIP}	Over-temp. protection			115 ± 5%		°C
U_{DCTRIP} [9]	U_{DC}-protection			1225 ± 2%		V
Mechanical Data						
M1	DC terminals, SI Units		4	–	6	Nm
M2	AC terminals, SI Units		8	–	10	Nm

SKiiPPACK â

SK integrated intelligent Power PACK halfbridge SKiiP 792 GB 170 - 373 CTV [7,9)]

Preliminary Data

Case S3



Features

- Short circuit protection, due to evaluation of current sensor signals
- Isolated power supply
- Low thermal impedance
- Optimal thermal management with integrated heatsink
- Pressure contact technology with increased power cycling capability, compact design
- Low stray inductance
- High power, small losses
- Over-temperature protection

1) $T_{heatsink}$ = 25 °C, unless otherwise specified
2) CAL = Controlled Axial Lifetime Technology (soft and fast)
3) without driver
4) Driver input to DC link / AC output to DC link / AC output to heatsink
5) with Semikron-DC link (low inductance)
6) other heatsinks on request
7) C - Integrated current sensors
   T - Temperature protection
   V - 15 V or 24 V power supply
8) AC connection busbars must be connected by the user; copper busbars available on request
9) options available for driver:
   U - DC link voltage sense
   F – Fiber optic connector
10) "$_s$" referenced to temperature sensor

